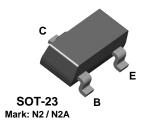


# **PN200 PN200A**

# **MMBT200** MMBT200A





# **PNP General Purpose Amplifier**

This device is designed for general purpose amplifier applications at collector currents to 300 mA. Sourced from Process 68.

#### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

| Symbol                            | Parameter  | Value       | Units |
|-----------------------------------|--|-------------|-------|
| $V_{CEO}$                         | Collector-Emitter Voltage                        | 45          | V     |
| V <sub>CBO</sub>                  | Collector-Base Voltage                           | 60          | V     |
| V <sub>EBO</sub>                  | Emitter-Base Voltage                             | 6.0         | V     |
| Ic                                | Collector Current - Continuous                   | 500         | mA    |
| T <sub>J</sub> , T <sub>stg</sub> | Operating and Storage Junction Temperature Range | -55 to +150 | °C    |

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
  2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
- 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

#### **Thermal Characteristics** TA = 25°C unless otherwise noted

| Symbol          | Characteristic                          | M               | Units                 |       |
|-----------------|---|-----------------|-----------------------|-------|
|                 |   | PN200<br>PN200A | *MMBT200<br>*MMBT200A |       |
| P <sub>D</sub>  | Total Device Dissipation                | 625             | 350                   | mW    |
|                 | Derate above 25°C                       | 5.0             | 2.8                   | mW/°C |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case    | 83.3            |                       | °C/W  |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | 200             | 357                   | °C/W  |

<sup>\*</sup>Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

# **PNP General Purpose Amplifier**

(continued)

## Electrical Characteristics TA = 25°C unless otherwise noted

| Symbol            | Parameter                            | Test Conditions                             | Min | Max | Units |
|-------------------|--------------------------------------|---|-----|-----|-------|
| OFFICHAE          | DACTEDISTICS                         |   |     |     |       |
|                   | RACTERISTICS                         | T   |     | 1   |       |
| BV <sub>CBO</sub> | Collector-Base Breakdown Voltage     | $I_C = 10 \mu\text{A},  I_B = 0$            | 60  |     | V     |
| BV <sub>CEO</sub> | Collector-Emitter Breakdown Voltage* | $I_C = 1.0 \text{ mA}, I_E = 0$             | 45  |     | V     |
| BV <sub>EBO</sub> | Emitter-Base Breakdown Voltage       | $I_E = 10 \mu\text{A},  I_C = 0$            | 6.0 |     | V     |
| I <sub>CBO</sub>  | Collector Cutoff Current             | $V_{CB} = 50 \text{ V}, I_{E} = 0$          |     | 50  | nA    |
| I <sub>CES</sub>  | Collector Cutoff Current             | V <sub>CE</sub> = 40 V, I <sub>E</sub> = 10 |     | 50  | nA    |
| I <sub>EBO</sub>  | Emitter Cutoff Current               | $V_{EB} = 4.0 \text{ V}, I_{C} = 0$         |     | 50  | nA    |

## **ON CHARACTERISTICS**

| h <sub>FE</sub>      | DC Current Gain                      | $I_C = 100 \mu A, V_{CE} = 1.0 V$   | 200<br>200A                 | 80<br>240                |                   |        |
|----------------------|--------------------------------------|---|-----------------------------|--------------------------|-------------------|--------|
|                      |                                      | $I_C = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}^*$ $I_C = 150 \text{ mA}, V_{CE} = 5.0 \text{ V}^*$ | 200<br>200A<br>200A<br>200A | 100<br>300<br>100<br>100 | 450<br>600<br>350 |        |
|                      |                                      | IC = 130 IIIA, VCE = 3.0 V  | 200A                        | 100                      |                   |        |
| $V_{\text{CE(sat)}}$ | Collector-Emitter Saturation Voltage | $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$<br>$I_C = 200 \text{ mA}, I_B = 20 \text{ mA}^*$  |                             |                          | 0.2<br>0.4        | V      |
| V <sub>BE(sat)</sub> | Base-Emitter Saturation Voltage      | I <sub>C</sub> = 10 mA, I <sub>B</sub> = 1.0 mA<br>I <sub>C</sub> = 200 mA, I <sub>B</sub> = 20 mA*   |                             |                          | 0.85<br>1.0       | V<br>V |

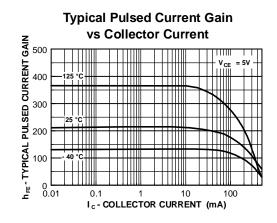
## SMALL SIGNAL CHARACTERISTICS

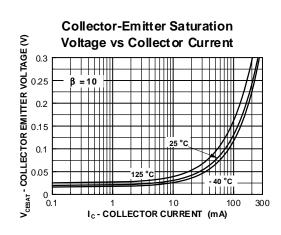
| f⊤               | Current Gain - Bandwidth Product | $V_{CE} = 20 \text{ V}, I_{C} = 20 \text{ mA}$   | 250 |     | MHz |
|------------------|----------------------------------|--|-----|-----|-----|
| C <sub>obo</sub> | Output Capacitance               | V <sub>CB</sub> = 10 V, f = 1.0 MHz              |     | 6.0 | pF  |
| NF               | Noise Figure                     | $I_C = 100 \mu\text{A},  V_{CE} = 5.0 \text{V},$ |     | 4.0 | dB  |
|                  |                                  | $R_G = 2.0 \text{ k}\Omega, f = 1.0 \text{ kHz}$ |     | 4.0 | dB  |

<sup>\*</sup>Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

**NOTE:** All voltages (V) and currents (A) are negative polarity for PNP transistors.

# **Typical Characteristics**

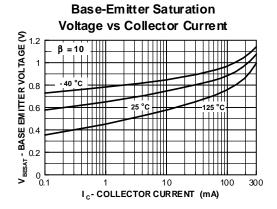


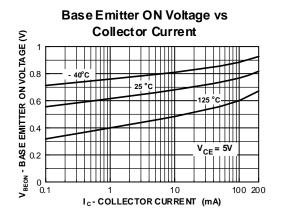


## **PNP General Purpose Amplifier**

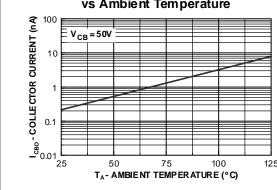
(continued)

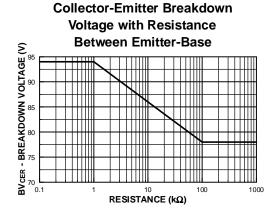
## Typical Characteristics (continued)

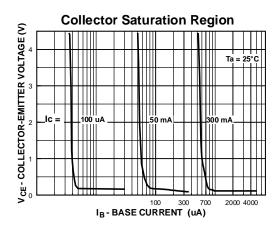


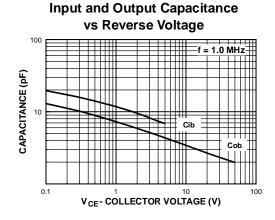








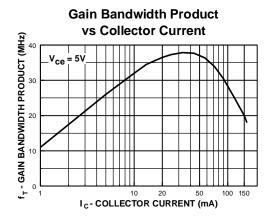


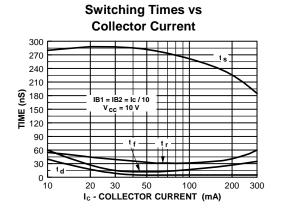


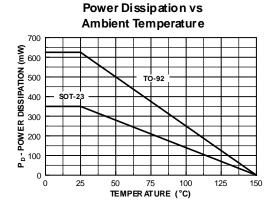
# **PNP General Purpose Amplifier**

(continued)

## Typical Characteristics (continued)





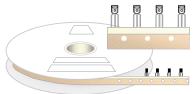


#### **TO-92 Tape and Reel Data** FAIRCHILD SEMICONDUCTOR TM **TO-92 Packaging** Configuration: Figure 1.0 **TAPE and REEL OPTION** FSCINT Label sample See Fig 2.0 for various Reeling Styles CBVK//418019 **FSCINT** Label 5 Reels per Intermediate Box Customized F63TNR Label sample Label F63TNR LOT: CBVK741B019 QTY: 2000 FSID: PN222N Customized QTY1: QTY2: Label 375mm x 267mm x 375mm Intermediate Box TO-92 TNR/AMMO PACKING INFROMATION **AMMO PACK OPTION** See Fig 3.0 for 2 Ammo Packing Style Quantity EOL code **Pack Options** 2,000 D26Z Е 2,000 D27Z Ammo М 2,000 D74Z D75Z 2,000 **FSCINT** Unit weight = 0.22 gm Reel weight with components = 1.04 kg Ammo weight with components = 1.02 kg Max quantity per intermediate box = 10,000 units Label 5 Ammo boxes per Intermediate Box 327mm x 158mm x 135mm Immediate Box Customized F63TNR Customized Label Label 333mm x 231mm x 183mm Intermediate Box (TO-92) BULK PACKING INFORMATION **BULK OPTION** See Bulk Packing DESCRIPTION QUANTITY Information table J18Z TO-18 OPTION STD 2.0 K / BOX Anti-static Bubble Sheets TO-5 OPTION STD NO LEAD CLIP 1.5 K / BOX J05Z **FSCINT Label** NO EOL TO-92 STANDARD STRAIGHT FOR: PKG 92, NO LEADCLIP 2.0 K / BOX 94 (NON PROELECTRON SERIES), 96 TO-92 STANDARD STRAIGHT FOR: PKG 94 (PROELECTRON SERIES BCXXX, BFXXX, BSRXXX), 97, 98 L34Z NO LEADCLIP 2.0 K / BOX 2000 units per 114mm x 102mm x 51mm EO70 box for std option Immediate Box 5 EO70 boxes per intermediate Box 530mm x 130mm x 83mm Customized Intermediate box Label FSCINT Label 10,000 units maximum per intermediate box for std option

## TO-92 Tape and Reel Data, continued

# **TO-92 Reeling Style Configuration:** Figure 2.0

## Machine Option "A" (H)

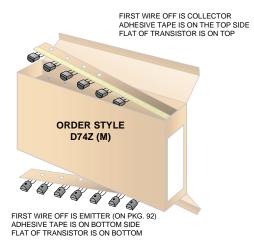


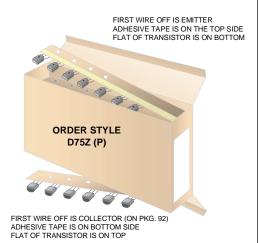
Style "A", D26Z, D70Z (s/h)

# Machine Option "E" (J)

Style "E", D27Z, D71Z (s/h)

# **TO-92 Radial Ammo Packaging Configuration:** Figure 3.0



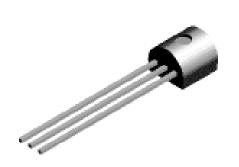


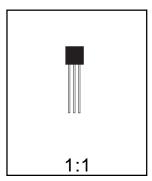


# **TO-92 Package Dimensions**



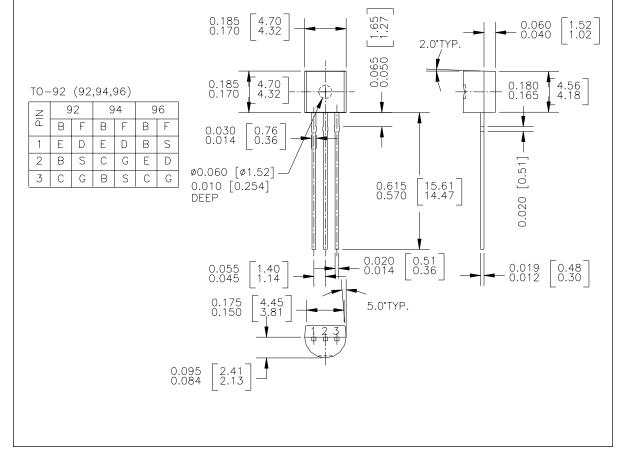
# TO-92 (FS PKG Code 92, 94, 96)

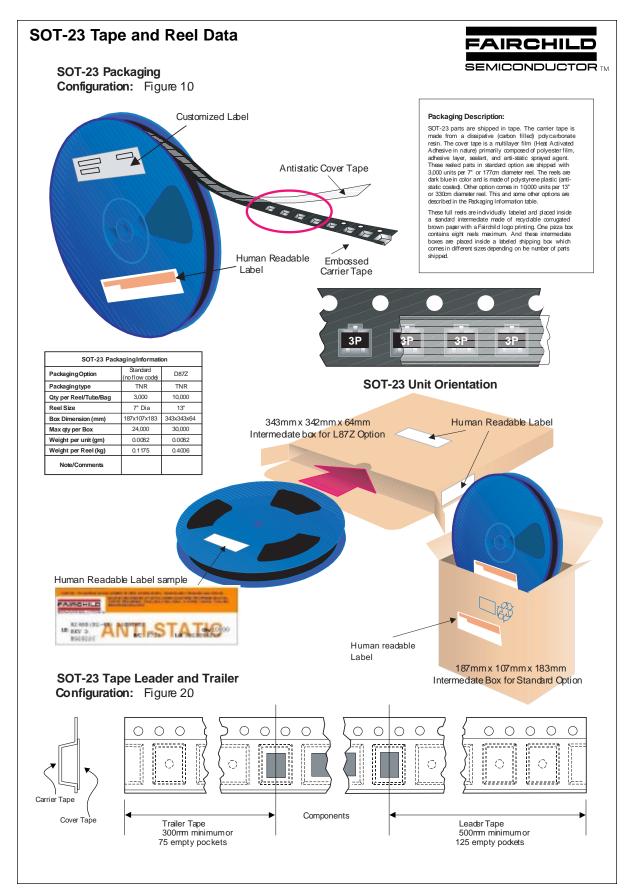




Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977

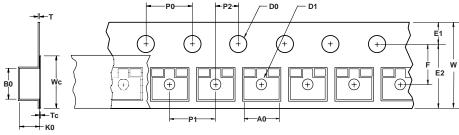




# SOT-23 Tape and Reel Data, continued

## **SOT-23 Embossed Carrier Tape**

Configuration: Figure 3.0



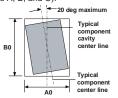
User Direction of Feed

|                     |                 |                 |               |                 | Di                | mension         | s are in n  | nillimete       | r             |               |                 |                   |               |                 |
|---------------------|-----------------|-----------------|---------------|-----------------|-------------------|-----------------|-------------|-----------------|---------------|---------------|-----------------|-------------------|---------------|-----------------|
| Pkg type            | Α0              | В0              | w             | D0              | D1                | E1              | E2          | F               | P1            | P0            | K0              | Т                 | Wc            | Тс              |
| <b>SOT-23</b> (8mm) | 3.15<br>+/-0.10 | 2.77<br>+/-0.10 | 8.0<br>+/-0.3 | 1.55<br>+/-0.05 | 1.125<br>+/-0.125 | 1.75<br>+/-0.10 | 6.25<br>min | 3.50<br>+/-0.05 | 4.0<br>+/-0.1 | 4.0<br>+/-0.1 | 1.30<br>+/-0.10 | 0.228<br>+/-0.013 | 5.2<br>+/-0.3 | 0.06<br>+/-0.02 |

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

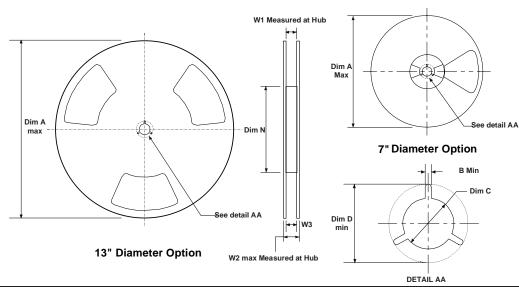


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

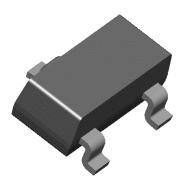
## SOT-23 Reel Configuration: Figure 4.0

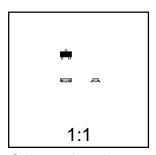


|           | Dimensions are in inches and millimeters |               |              |                                   |               |             |                                   |               |                             |
|-----------|--|---------------|--------------|-----------------------------------|---------------|-------------|-----------------------------------|---------------|-----------------------------|
| Tape Size | Reel<br>Option                           | Dim A         | Dim B        | Dim C                             | Dim D         | Dim N       | Dim W1                            | Dim W2        | Dim W3 (LSL-USL)            |
| 8mm       | 7" Dia                                   | 7.00<br>177.8 | 0.059<br>1.5 | 512 +0.020/-0.008<br>13 +0.5/-0.2 | 0.795<br>20.2 | 2.165<br>55 | 0.331 +0.059/-0.000<br>8.4 +1.5/0 | 0.567<br>14.4 | 0.311 - 0.429<br>7.9 - 10.9 |
| 8mm       | 13" Dia                                  | 13.00<br>330  | 0.059<br>1.5 | 512 +0.020/-0.008<br>13 +0.5/-0.2 | 0.795<br>20.2 | 4.00<br>100 | 0.331 +0.059/-0.000<br>8.4 +1.5/0 | 0.567<br>14.4 | 0.311 - 0.429<br>7.9 - 10.9 |



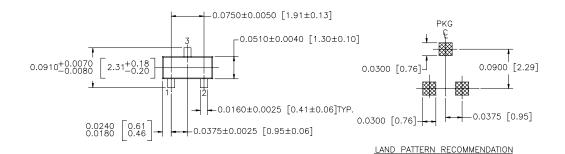
# SOT-23 (FS PKG Code 49)

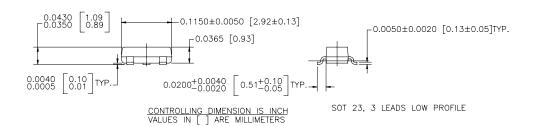




Scale 1:1 on letter size paper Dimensions shown below are in:

inches [millimeters]
Part Weight per unit (gram): 0.0082





NOTE: UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

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- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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|--------------------------|---------------------------|---|
| Advance Information      | Formative or<br>In Design | This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.  |
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